

• General Description

The ZM062N03N combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

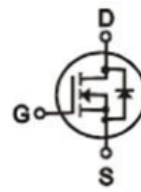
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Ordering Information:

Part NO.	ZM062N03N
Marking	ZM062N03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

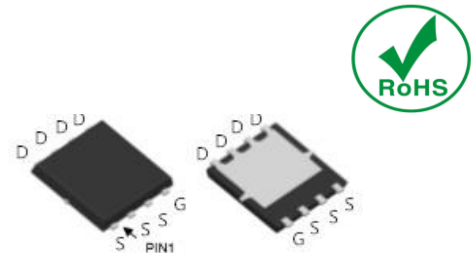
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ\text{C}$	55	A
	$I_D @ T_C = 75^\circ\text{C}$	42	A
	$I_D @ T_C = 100^\circ\text{C}$	35	A
	$I_D @ T_A = 25^\circ\text{C}$	18	A
	$I_D @ T_A = 70^\circ\text{C}$	14	A
Pulsed Drain Current ①	I_{DM}	140	A
Total Power Dissipation	$P_D @ T_C = 25^\circ\text{C}$	62.5	W
Total Power Dissipation	$P_D @ T_A = 25^\circ\text{C}$	2.7	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$

• Product Summary


$V_{DS} = 30\text{V}$

$R_{DS(ON)} = 6.2\text{m}\Omega$

$I_D = 55\text{A}$



DFN5x6

Storage Temperature	T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E_{AS}	110	mJ
Diode continuous forward current	$I_S@T_C=25^\circ C$	55	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.0	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	46	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		6.2	8.5	m Ω
		$V_{GS}=4.5V, I_D=10A$		10	12	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$		5.4		s
Source-drain voltage	V_{SD}	$I_S=20A$		0.83	1.2	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	1150	1380	pF
Output capacitance	C_{oss}		-	230	276	
Reverse transfer capacitance	C_{rss}		-	113	135	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R_g	f = 1MHz		1.8		Ω
Total gate charge	Q_g	$V_{DD}=25V$	-	12	-	nC

Gate - Source charge	Q_{gs}	$I_D = 5A$ $V_{GS} = 10V$	-	4	-	
Gate - Drain charge	Q_{gd}		-	6	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V$ $R_G = 3.3\Omega, I_D=15A$		4.5		ns
Turn-ON Rise time	t_r			12		ns
Turn-Off Delay time	$t_{D(off)}$			26		ns
Turn-Off Fall time	t_f			7.5		ns
Reverse Recovery Time	t_{RR}	$V_{DD} = 20 V,$ $dI_S/dt = 100 A/s,$ $I_S = 15A$		9.7		ns
Charge Time	t_a			5.8		ns
Discharge Time	t_b			4.1		ns
Reverse Recovery Charge	Q_{RR}			2.9		nC

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Power Dissipation

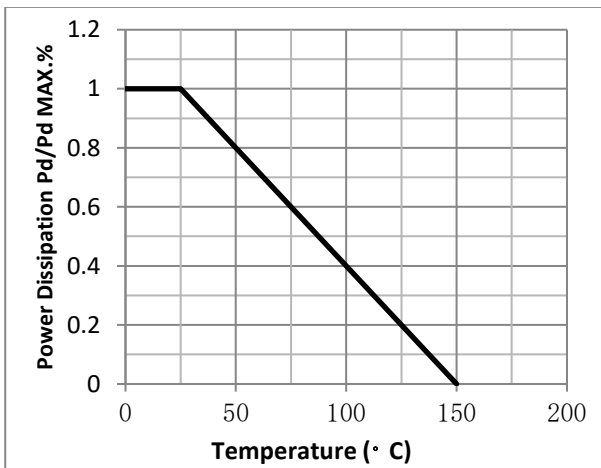


Fig.2 Typical output Characteristics

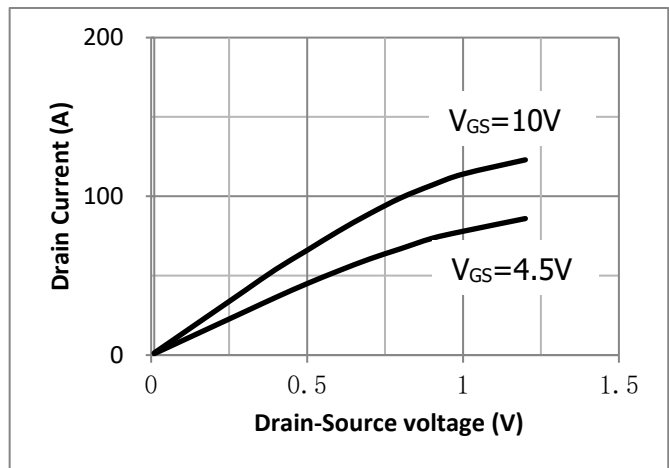


Fig.3 Threshold Voltage V.S Junction Temperature

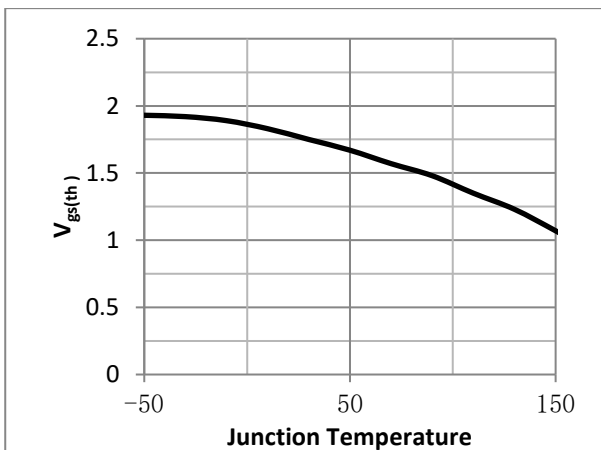


Fig.4 Resistance V.S Drain Current

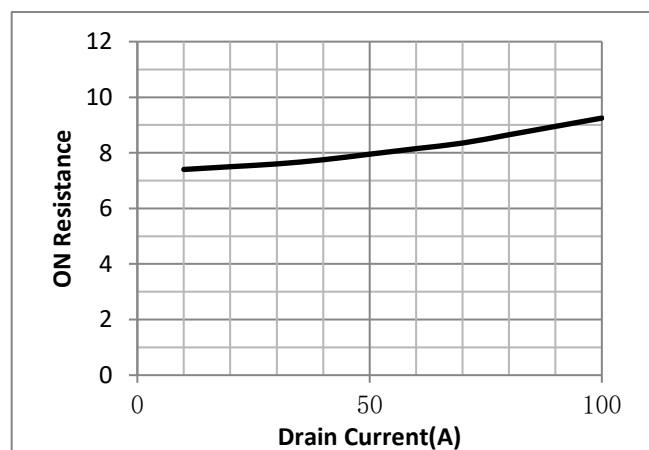


Fig.5 On-Resistance VS Gate Source Voltage

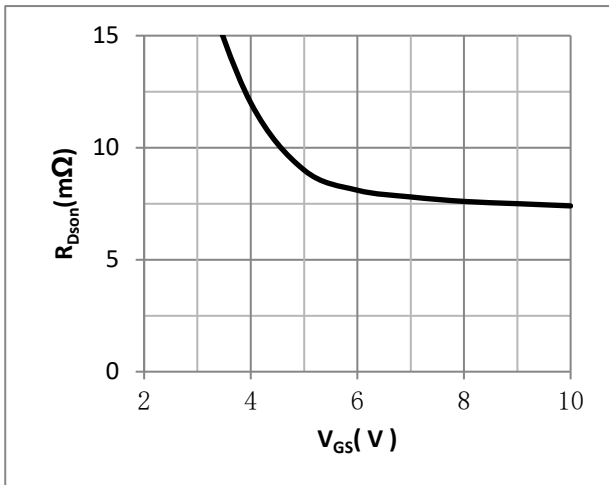


Fig.6 On-Resistance V.S Junction Temperature

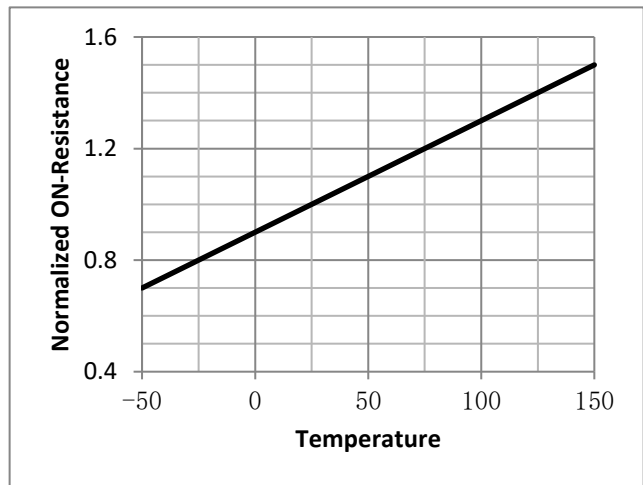


Fig.7 SOA Maximum Safe Operating Area

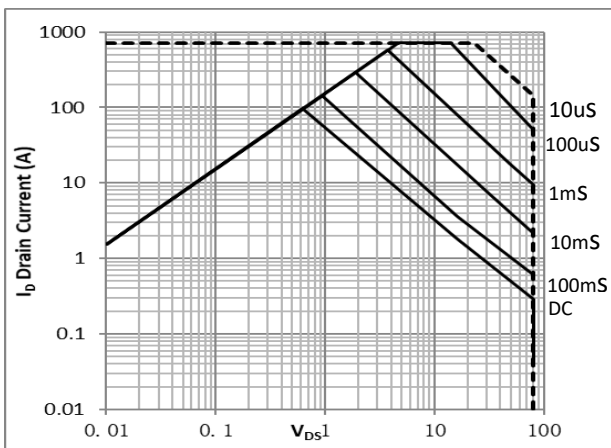


Figure 8. Diode Forward Voltage vs. Current

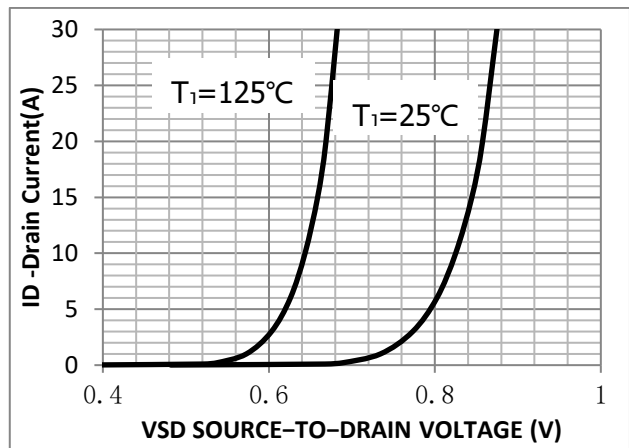


Figure 9. Transfer Characteristics

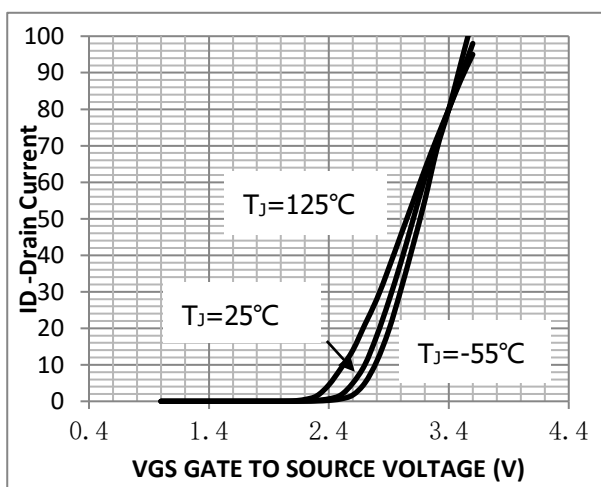


Fig.10 Typical output Characteristics

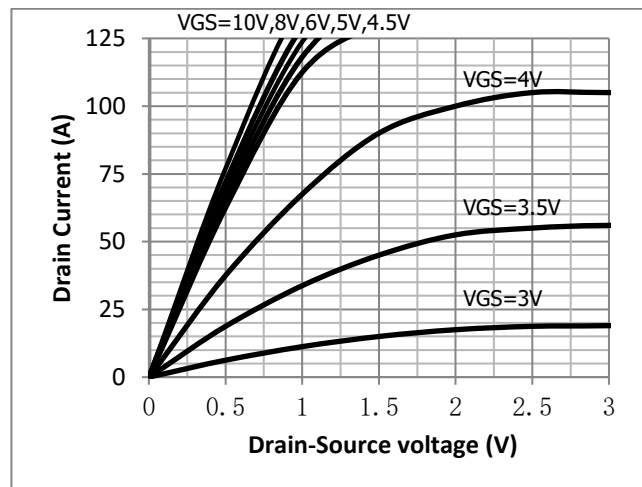


Fig.11 I_D V.S Junction Temperature

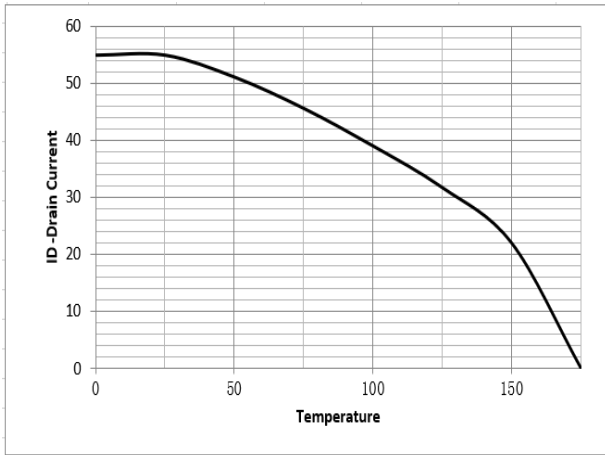


Fig.12 Switching Time Measurement Circuit

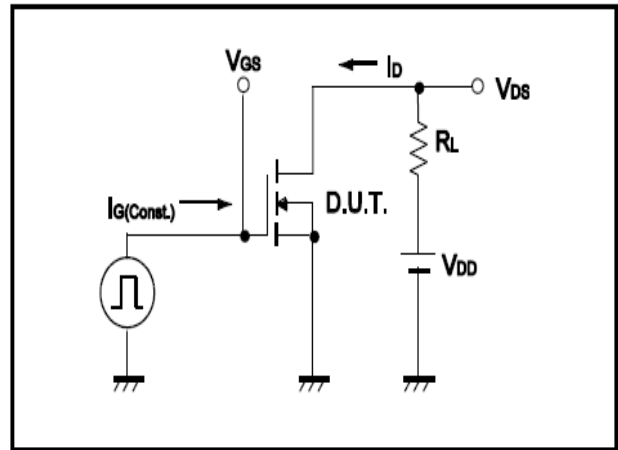


Fig.13 Gate Charge Waveform

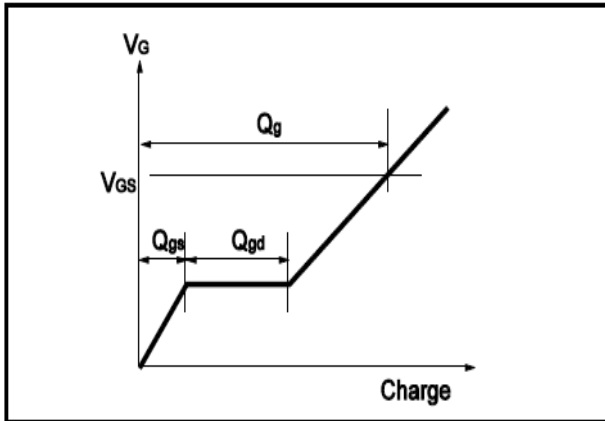


Fig.14 Avalanche Waveform

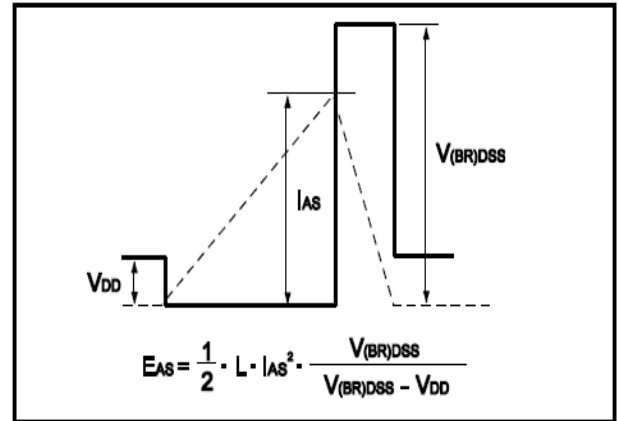


Fig.15 Resistive Switching Test Circuit

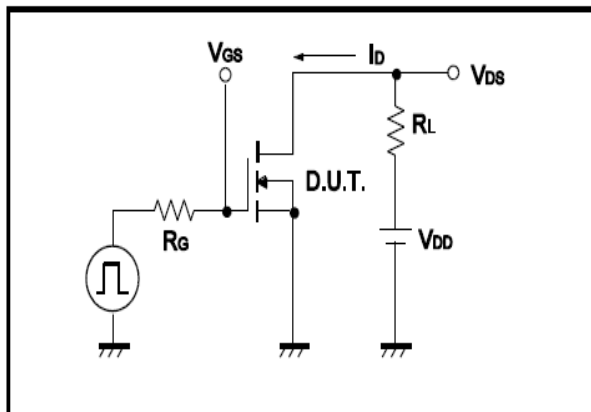


Fig.16 Resistive Switching Test Waveform

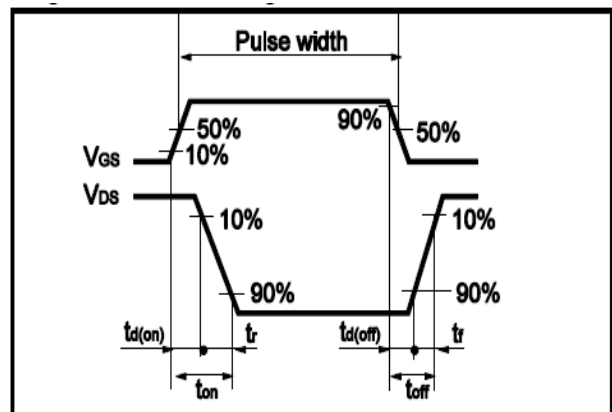
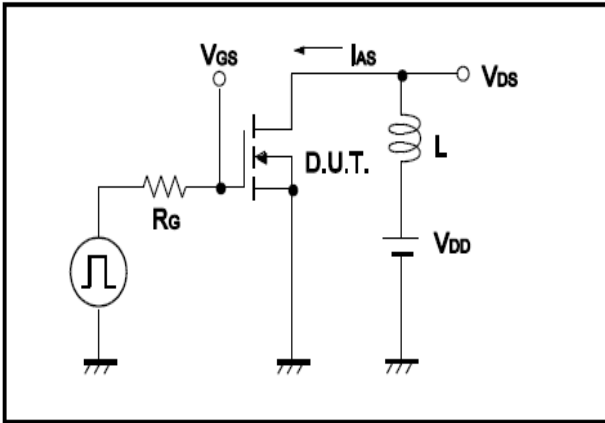


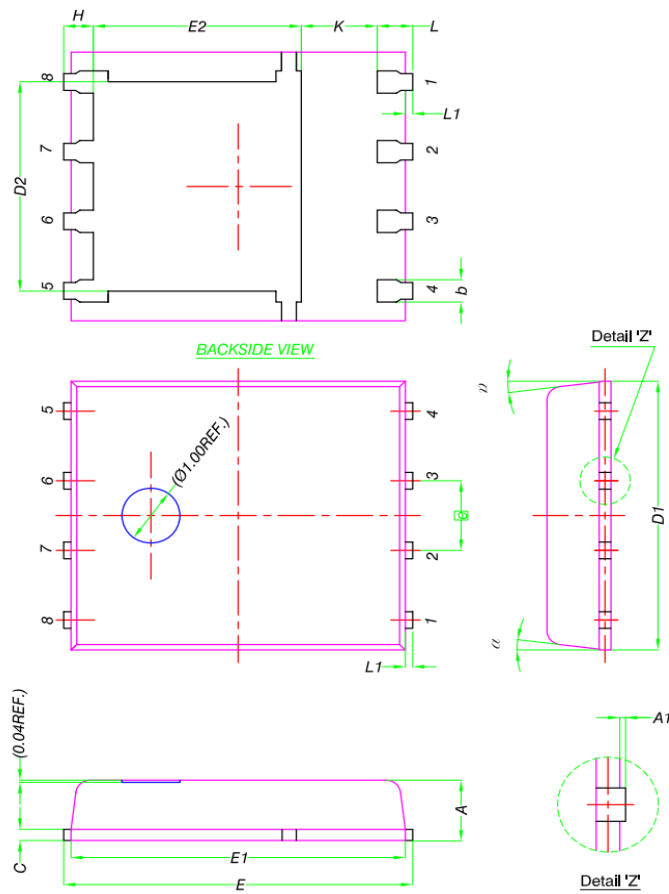
Fig.17 Avalanche Measurement Circuit





•Dimensions (DFN5×6)

Unit: mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°